

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = +25^\circ C$
60V	68m Ω @ $V_{GS} = 10V$	8.5A
	100m Ω @ $V_{GS} = 4.5V$	7.0A

Description

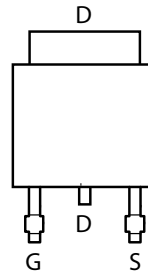
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

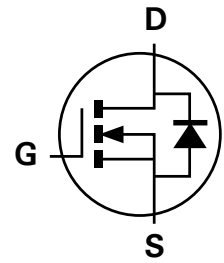
- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply



TOP VIEW



PIN OUT - TOP VIEW



Equivalent Circuit

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

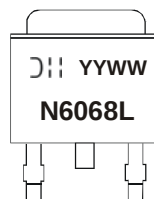
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN6068LK3-13	N6068L	13	16	2,500

- Note:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
 N6068L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 09 = 2009)
 WW = Week (01-52)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

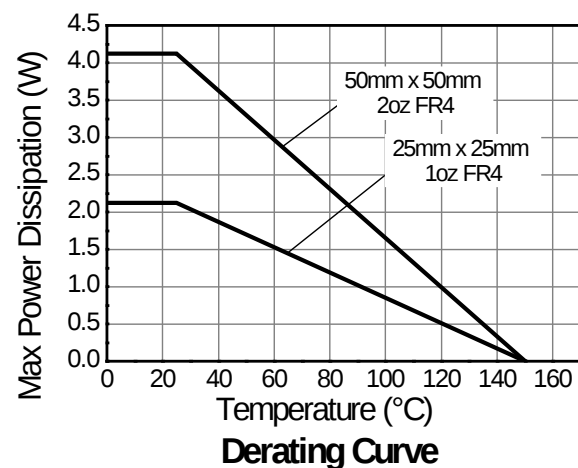
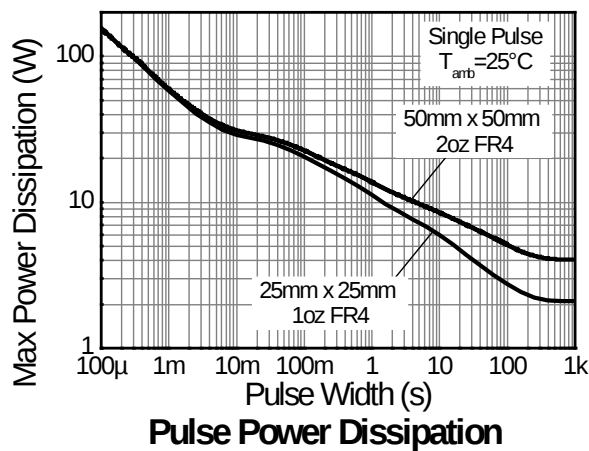
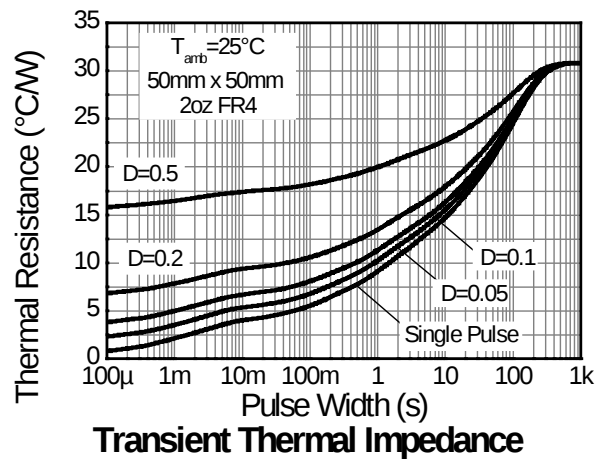
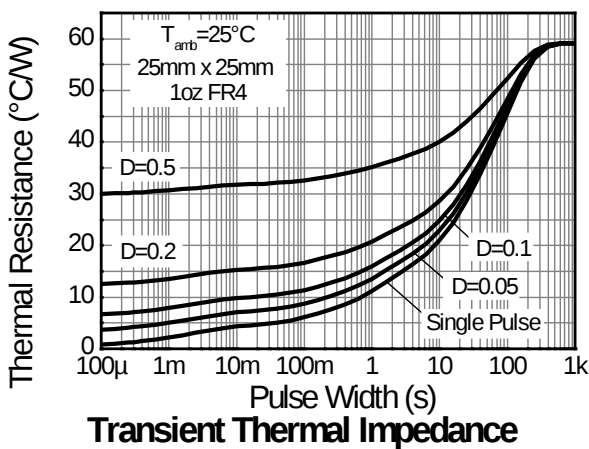
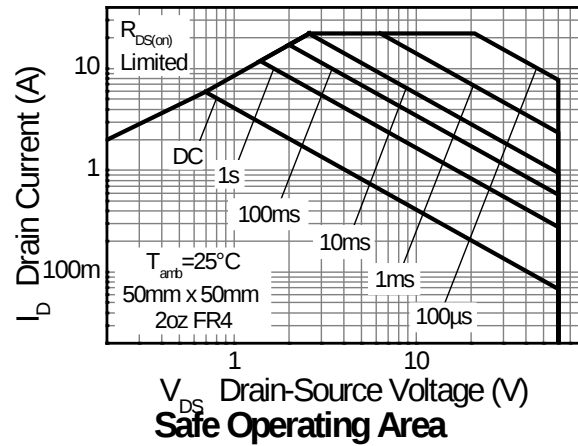
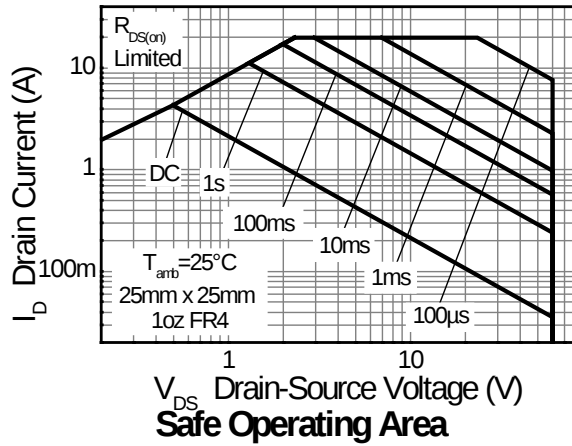
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V _{DSS}	60	V
Gate-Source voltage	(Note 5)		V _{GS}	±20	V
Single Pulsed Avalanche Energy	(Note 11)		E _{AS}	37.5	mJ
Single Pulsed Avalanche Current	(Note 11)		I _{AS}	5.0	A
Continuous Drain current	V _{GS} = 10V	(Note 7)	I _D	8.5	A
		T _A = 70°C (Note 7)		6.8	
		(Note 6)		6.0	
Pulsed Drain current	V _{GS} = 10V	(Note 8)	I _{DM}	22.2	A
Continuous Source current (Body diode)	(Note 7)		I _S	10.2	A
Pulsed Source current (Body diode)	(Note 8)		I _{SM}	22.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 6)	P _D	4.12	W mW/°C
			33	
	(Note 7)		8.49	
	(Note 9)		67.9	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	2.12	°C/W
	(Note 7)		16.9	
	(Note 9)		30.3	
Thermal Resistance, Junction to Lead	(Note 10)	R _{θJL}	14.7	°C/W
			59.0	
Operating and storage temperature range		T _J , T _{STG}	-55 to +150	°C

- Notes:
- AEC-Q101 V_{GS} maximum is ±16V.
 - For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Same as note 2, except the device is measured at t ≤ 10 sec.
 - Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
 - For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Thermal resistance from junction to solder-point (at the end of the drain lead).
 - UIS in production with L = 3.0mH, I_{AS} = 5.0A, R_G = 25•, V_{DD} = 50V, starting T_J = 25°C

Thermal Characteristics

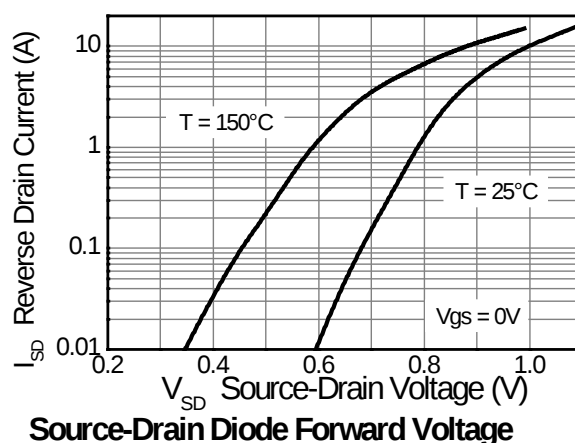
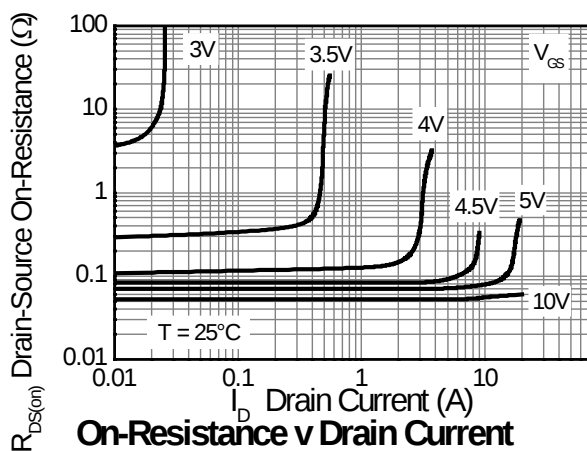
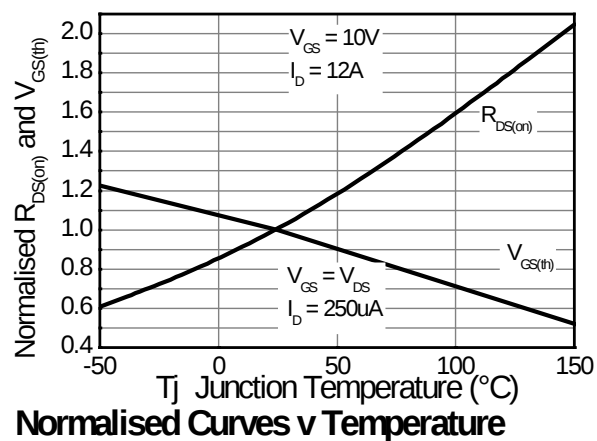
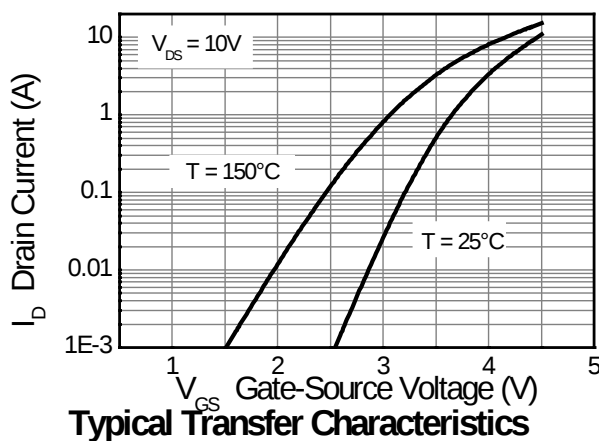
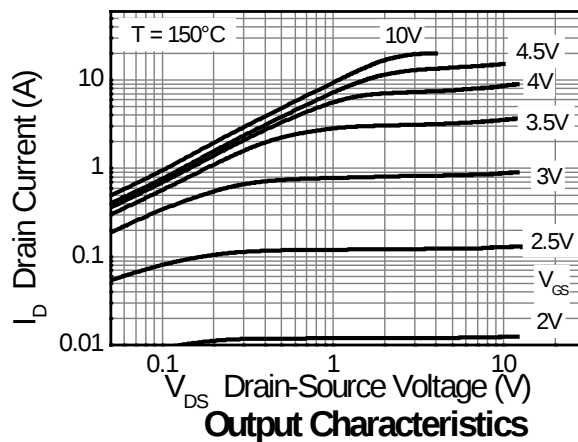
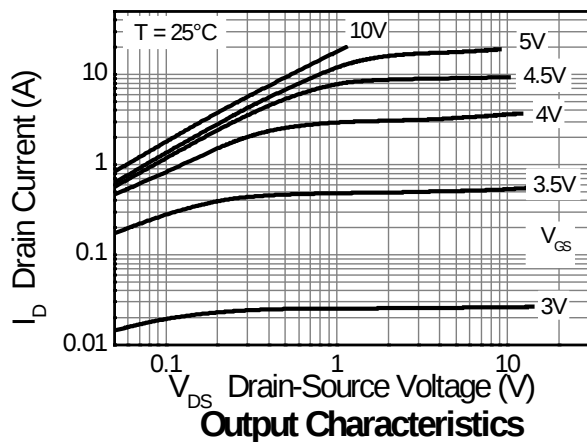


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

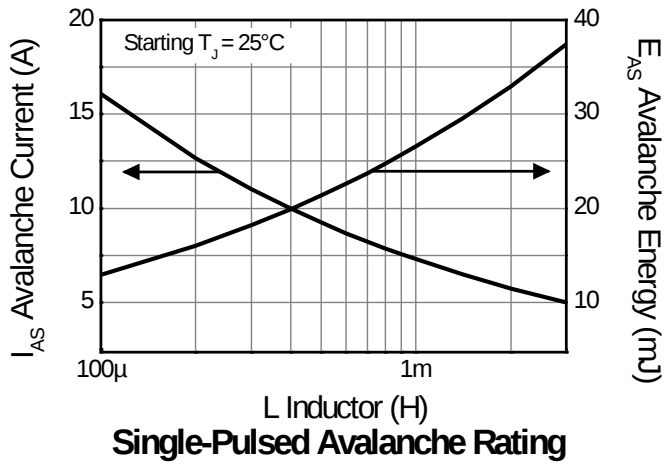
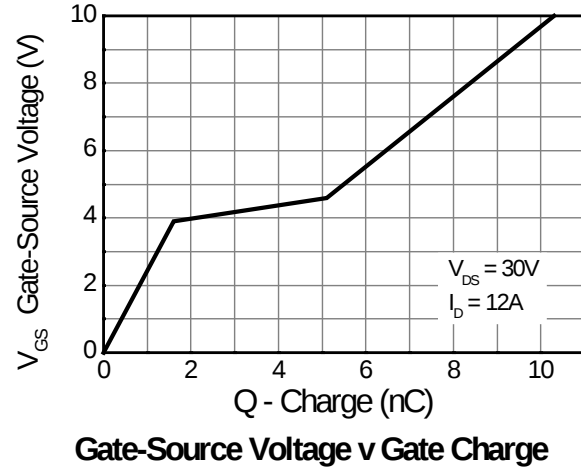
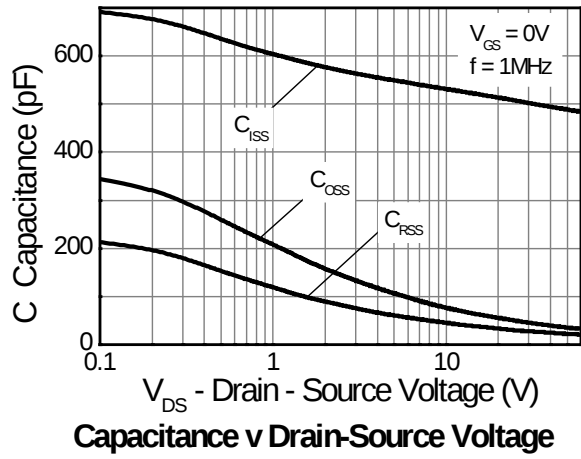
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	I _D = 250μA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	I _D = 250μA, V _{DS} = V _{GS}	
Static Drain-Source On-Resistance (Note 12)	R _{DS (ON)}	—	—	0.068	Ω	V _{GS} = 10V, I _D = 12A	
				0.100		V _{GS} = 4.5V, I _D = 6A	
Forward Transconductance (Notes 12 & 13)	g _{fs}	—	19.7	—	S	V _{DS} = 15V, I _D = 12A	
Diode Forward Voltage (Note 12)	V _{SD}	—	0.98	1.15	V	I _S = 12A, V _{GS} = 0V	
Reverse recovery time (Note 13)	t _{rr}		145	—	ns	I _S = 12A, di/dt= 100A/μs	
Reverse recovery charge (Note 13)	Q _{rr}	—	929	—	nC		
DYNAMIC CHARACTERISTICS (Note 13)							
Input Capacitance	C _{ISS}	—	502	—	pF	V _{DS} = 30V, V _{GS} = 0V f= 1MHz	
Output Capacitance	C _{OSS}	—	45.7	—	pF		
Reverse Transfer Capacitance	C _{RSS}	—	27.1	—	pF		
Total Gate Charge	Q _g	—	5.55	—	nC	V _{GS} = 4.5V	V _{DS} = 30V I _D = 12A
Total Gate Charge	Q _g	—	10.3	—	nC	V _{GS} = 10V	
Gate-Source Charge	Q _{gs}	—	1.6	—	nC		
Gate-Drain Charge	Q _{gd}	—	3.5	—	nC		
Turn-On Delay Time (Note 14)	t _{D(on)}	—	3.6	—	ns	V _{DD} = 30V, V _{GS} = 10V I _D = 12A, R _G ≅ 6.0Ω	
Turn-On Rise Time (Note 14)	t _r	—	10.8	—	ns		
Turn-Off Delay Time (Note 14)	t _{D(off)}	—	11.9	—	ns		
Turn-Off Fall Time (Note 14)	t _f	—	8.7	—	ns		

Notes: 12. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
13. For design aid only, not subject to production testing.
14. Switching characteristics are independent of operating junction temperatures.

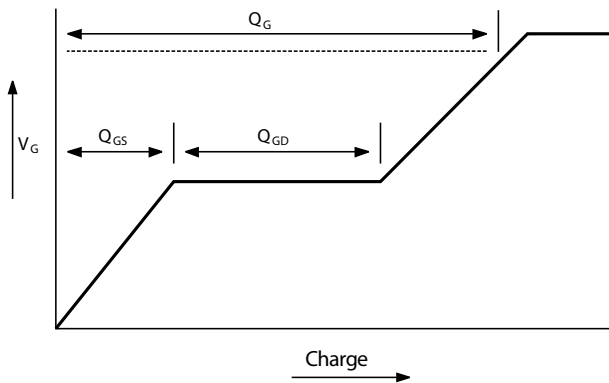
Typical Characteristics



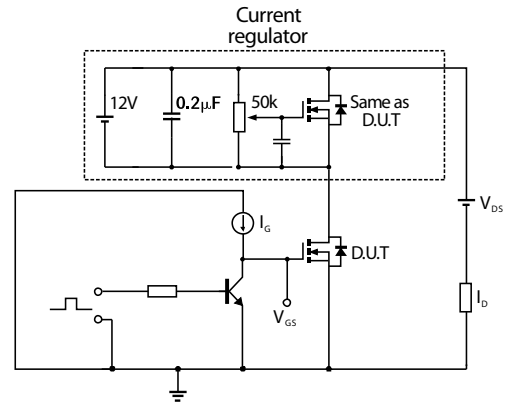
Typical Characteristics - continued



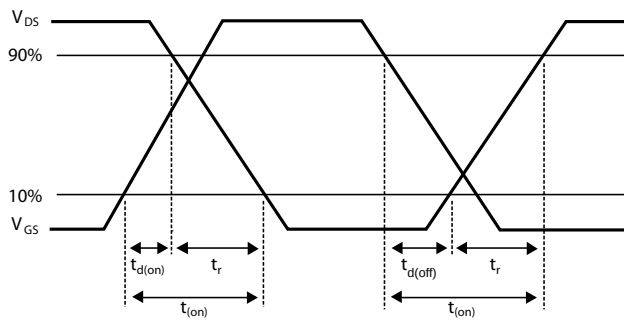
Test Circuits



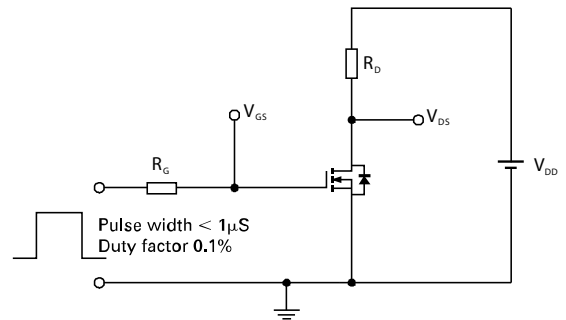
Basic gate charge waveform



Gate charge test circuit



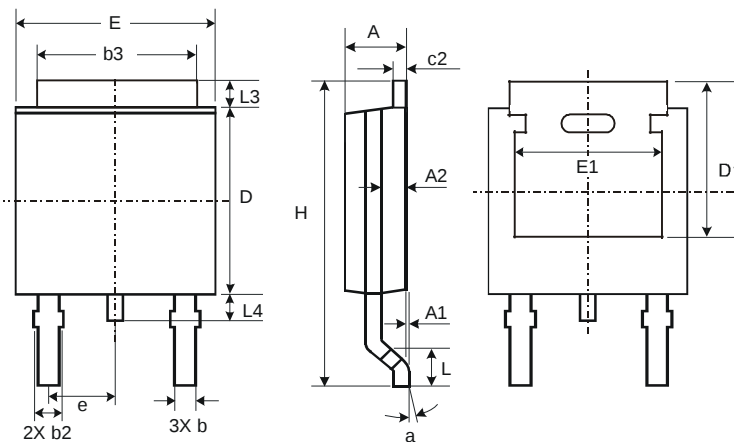
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

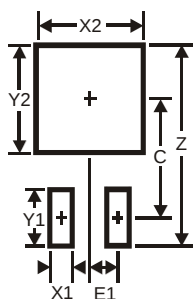
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

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